9. The method of claim 1, wherein the graphene film is selected from the group consisting of monolayer graphene, few-layer graphene, double-layer graphene, triple-layer graphene, multilayer graphene, and combinations thereof.

10. The method of claim 1, wherein the graphene film excludes reduced graphene oxide.

11. The method of claim 1, wherein the graphene film excludes graphite.

12. The method of claim 1, wherein the metal is selected from the group consisting of iron, nickel, cobalt, palladium, platinum, gold, ruthenium, rhodium, iridium, alloys thereof, and combinations thereof.

13. The method of claim 1, wherein the metal comprises iron.

14. The method of claim 1, wherein the buffer is selected from the group consisting of aluminum, magnesium, silicon, ~~alloys thereof, derivatives thereof,~~ and combinations thereof.

15. The method of claim 1, wherein the buffer comprises aluminum oxide.

16. The method of claim 1, wherein the buffer has a thickness between about 1 nm to about 10 nm.

17. The method of claim 1, wherein the metal has a thickness of about 1 nm.

18. The method of claim 1, wherein the applying comprises:
depositing the metal onto a surface of the graphene film; and
depositing the buffer onto a surface of the metal.

19. The method of claim 1, wherein the applying occurs by electron beam deposition.